

GaP – UV-Photodiodes (150 - 550 nm)**EPD-150-0****Schottky barrier type****Description**

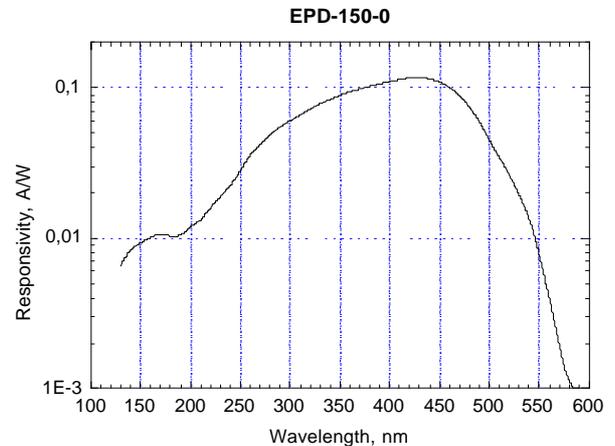
Wide bandwidth and high spectral sensitivity in the UV and visible ranges (150 nm - 550 nm), low cost, chip based on GaP, large active areas are possible

Applications

Medical engineering (dermatology), output check of UV - lamps and gas burner flame, measurement and control of ecological parameters, radiation control for a solarium, UV water purification facilities

Features

Mounted in hermetically sealed TO-packages with sapphire window, different active areas are available



Parameter	Units	Symbol	EPD-150-0/2.5	EPD-150-0/3.6
Chip sizes	mm		2.46 x 2.46	3.56 x 3.56
Active area	mm ²	A	4.8	10.9
Max. dark current at $V_R = 0,01V$ $V_R = 1V$	pA	I_D	4 40	8 80
Package			TO-39	TO-39
Spectral range at 0,01 maximum	nm	$\lambda_{min}-\lambda_{max}$	150 – 550 (with sapphire window)	
Spectral bandwidth at 50%	nm	$\Delta\lambda_{0,5}$	180	
Peak sensitivity wavelength	nm	λ_p	440	
Typical responsivity at λ_p	A/W	$S_{\bar{e}}$	0.12	
Temperature coefficient of I_D	times/K	TCI_D	1.07	
Typical rise and fall time at $V_R = 5V$ and 50 Ω load	ns	t_r t_f	1 140	1 140
Maximal reverse voltage at $I_R=100 \mu A$	V	V_R	10	
Operating temperature range	°C	T_{amb}	-40 to +125	
Storage temperature range	°C	T_{stg}	-40 to +125	

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